

Masanori Nagase

List of Publications by Year in descending order

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21
papers

435
citations

933447

10
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794594

19
g-index

21
all docs

21
docs citations

21
times ranked

301
citing authors

#	ARTICLE	IF	CITATIONS
1	High temperature application of diamond power device. Diamond and Related Materials, 2012, 24, 201-205.	3.9	133
2	Cross-phase-modulation-based wavelength conversion using intersubband transition in InGaAs/AlAs/AlAsSb coupled quantum wells. Optics Letters, 2007, 32, 751.	3.3	68
3	All-optical demultiplexing of 160 Gbit/s signals with Mach-Zehnder interferometric switch utilizing intersubband transition in InGaAs/AlAsSb quantum well. Applied Physics Letters, 2007, 91, 221115.	3.3	62
4	Mechanism of ultrafast modulation of the refraction index in photoexcited $\ln \left(\frac{1 + \frac{25}{x}}{1 + \frac{25}{x}} \right)$ Physical Review B, 2008, 78, .	3.2	25
5	Ultrafast All-Optical Refractive Index Modulation in Intersubband Transition Switch Using InGaAs/AlAs/AlAsSb Quantum Well. Japanese Journal of Applied Physics, 2007, 46, L157-L160.	1.5	24
6	Bistability Characteristics of GaN/AlN Resonant Tunneling Diodes Caused by Intersubband Transition and Electron Accumulation in Quantum Well. IEEE Transactions on Electron Devices, 2014, 61, 1321-1326.	3.0	22
7	Vertical Diamond Schottky Barrier Diode Fabricated on Insulating Diamond Substrate Using Deep Etching Technique. IEEE Transactions on Electron Devices, 2013, 60, 1416-1420.	3.0	14
8	Investigating the bistability characteristics of GaN/AlN resonant tunneling diodes for ultrafast nonvolatile memory. Japanese Journal of Applied Physics, 2015, 54, 034201.	1.5	14
9	Enhancement of All-Optical Cross Phase Modulation in InGaAs/AlAsSb Coupled Quantum Wells Using InAlAs Coupling Barriers. IEEE Photonics Technology Letters, 2008, 20, 2183-2185.	2.5	11
10	All-Optical Demultiplexing from 160 to 40/80 Gb/s Using Mach-Zehnder Switches Based on Intersubband Transition of InGaAs/AlAsSb Coupled Double Quantum Wells. IEICE Transactions on Electronics, 2009, E92-C, 187-193.	0.6	11
11	Diamond Vertical Schottky Barrier Diode with Al ₂ O ₃ Field Plate. Materials Science Forum, 0, 717-720, 1319-1321.	0.3	10
12	Resistance switching memory operation using the bistability in current-voltage characteristics of GaN/AlN resonant tunneling diodes. Japanese Journal of Applied Physics, 2016, 55, 100301.	1.5	9
13	Phase-Breaking Effect Appearing in the Current-Voltage Characteristics of Double-Barrier Resonant Tunneling Diodes –Theoretical Fitting Over Four Orders of Magnitude–. Japanese Journal of Applied Physics, 2001, 40, 3018-3022.	1.5	6
14	Stabilization of nonvolatile memory operations using GaN/AlN resonant tunneling diodes by reducing structural inhomogeneity. Japanese Journal of Applied Physics, 2018, 57, 070310.	1.5	6
15	Photoreflectance study of InGaAs/AlAsSb quantum wells grown by molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 177-180.	1.5	5
16	Strain compensation for InGaAs/AlAsSb coupled double quantum wells by controlling the barrier layer composition. Journal of Crystal Growth, 2007, 301-302, 240-243.	1.5	5
17	Ultrafast All-Optical Gating Operation Using Michelson Interferometer for Hybrid Integration of Intersubband Transition Switch on Si Platform. IEEE Photonics Technology Letters, 2011, 23, 1884-1886.	2.5	4
18	Switching characteristics of nonvolatile memory using GaN/AlN resonant tunneling diodes. Japanese Journal of Applied Physics, 2019, 58, 091001.	1.5	3

#	ARTICLE	IF	CITATIONS
19	Selective-Area Growth of Thick Diamond Films Using Chemically Stable Masks of Ru/Au and Mo/Au. Japanese Journal of Applied Physics, 2012, 51, 070202.	1.5	2
20	Growth and Characterization of GaN/AlN Resonant Tunneling Diodes for High-Performance Nonvolatile Memory. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000495.	1.8	1
21	Intersubband transitions in InGaAs/AlAsSb coupled double quantum wells with InAlAs coupling barriers. , 2007, , .		0